NOV 2018 Version1.0

Ascend Semicondutor	CoLtd
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ASDM30P30CTD

-30V P-Channel MOSFET

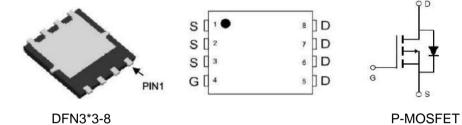
Features

- Low RDS(ON)
- Fast switching
- Green Device Available

Application

- MB / VGA / Vcore
- POL Applications

	-	Rons
Vdss	-30	V
RDS(ON)-Typ.	15	mΩ
ID	-30	A



Absolute Maximum Ratings (TJ=25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
VDSS	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	V
TJ	Maximum Junction Temperature		150	C°
Tstg	Storage Temperature Range		-55 to 150	°C
ls	Diode Continuous Forward Current		-30	А
I Dм ^①	Pulse Drain Current Tested	Tc=25°C	-60	А
D	Continuous Drain Current	Tc=25°C	-30	А
טו		Tc=100°C	-19	~
PD	Maximum Power Dissipation	T₀=25°C	17	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit	
Rejc	Thermal Resistance-Junction to Case	Steady State	4.6	°C/W
Reja	Thermal Resistance-Junction to Ambient	Steady State	62	°C/W

Note ① : Max. current is limited by bonding wire

Note O : UIS tested and pulse width are limited by maximum junction temperature 150°C

Note 3 : Surface Mounted on 1in 2 FR-4 board with 1oz.



Product Summary

Electrical Characteristics (TJ=25°C Unless Otherwise Noted)

1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	Condition	Min.	Тур	Max.	Unit
BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30			v
V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2		-2.5	V
t I _{DSS}	V _{DS} =-30V, V _{GS} =0V	_		-1,0	uA
t I _{GSS}	V _{GS} =±12V ,V _{DS} =0V			±100	nA
	V _{GS} =-10V, I _D =-9A		15	20	mΩ
KDS(ON)	V _{GS} =-4.5V, I _D =-8A		25	32	mΩ
g _{FS}	V _{DS} =-10V, I _D =-5A		9		s
	V _{GS(TH)} t I _{DSS} t I _{GSS} R _{DS(ON)}	$V_{GS(TH)} = V_{GS} = V_{DS}, I_D = -250 uA$ $t = I_{DSS} = V_{DS} = -30V, V_{GS} = 0V$ $t = I_{GSS} = V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = -10V, I_D = -9A$ $V_{GS} = -4.5V, I_D = -8A$	$\frac{V_{GS(TH)}}{V_{GS}(TH)} = \frac{V_{GS} = V_{DS}, I_D = -250uA}{V_{DS} = -30V, V_{GS} = 0V} - 1.2$ $\frac{V_{DSS}}{V_{DS} = -30V, V_{GS} = 0V} = \frac{V_{GS} = \pm 12V, V_{DS} = 0V}{V_{GS} = -10V, I_D = -9A} = \frac{V_{GS} = -10V, I_D = -9A}{V_{GS} = -4.5V, I_D = -8A} = \frac{1000}{V_{GS} = -4.5V, I_D = -4.$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Тур	Max.	Unit
Input capacitance	Ciss		-	1650	- 21	
Output capacitance	Coss	f = 1MHz	-	330	-	pF
Reverse transfer capacitance	Crss		-	220		

•Gate Charge characteristics(Ta = 25°C)

Parameter	Symbol	Condition	Min.	Тур	Max.	Unit
Total gate charge	Qg	VDD =25V		15	-	
Gate - Source charge	Qgs	ID = 8A	-	4	-	nC
Gate - Drain charge	Qgd	VGS = 10V	-	6	_	

Note: 1) Pulse Test : Pulse width \leq 300µs, Duty cycle \leq 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;





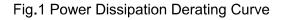
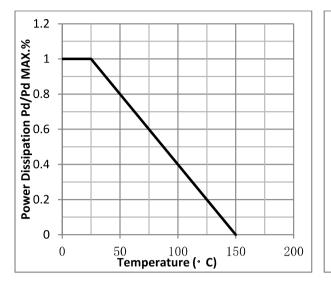


Fig.2 Typical output Characteristics



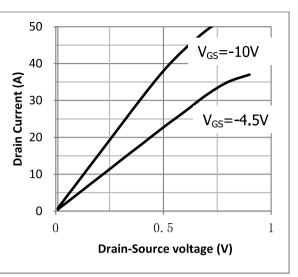


Fig.3 Threshold Voltage V.S Junction Temperature

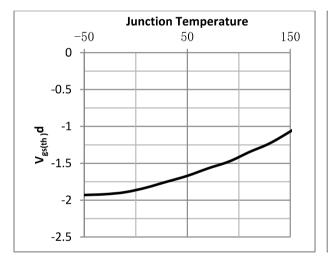


Fig.4 Resistance V.S Drain Current

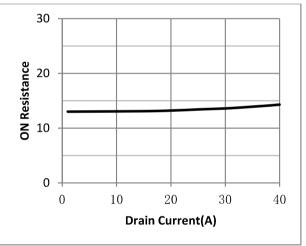


Fig.5 On-Resistance VS Gate Source Voltage

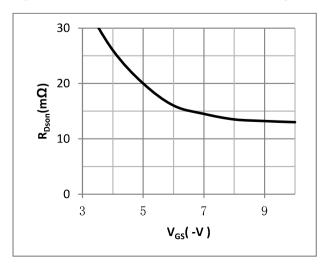
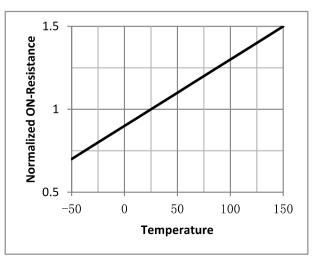


Fig.6 On-Resistance V.S Junction Temperature





ASDM30P30CTD

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Fig.7 Switching Time Measurement Circuit

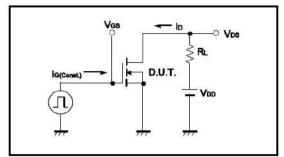


Fig.8 Gate Charge Waveform

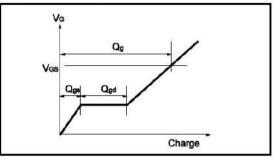
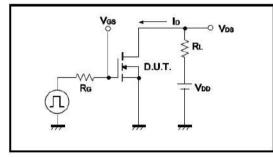


Fig.9 Switching Time Measurement Circuit





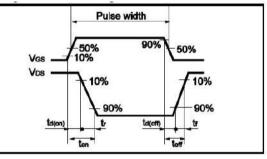
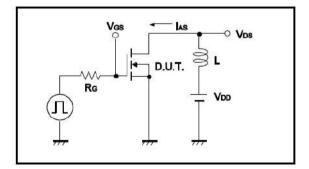
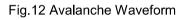
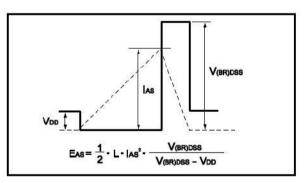


Fig.11 Avalanche Measurement Circuit









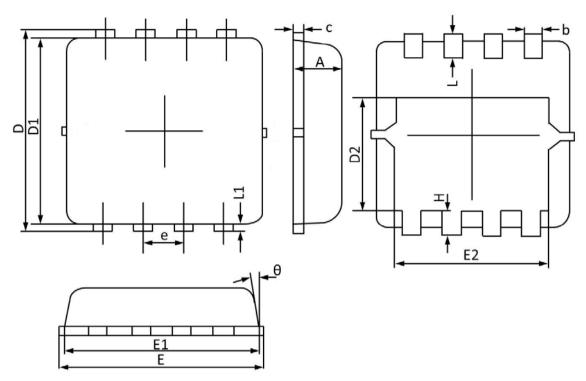
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity
ASDM30P30CTD-R	30P30C	DFN3*3-8	Tape Reel	5000

PACKAGE	MARKING
DFN3*3-8	AS □□□ 30P30C □□□□ ► Date Code



DFN3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimension	s In Inches
Symbol	MAX	MIN	MAX	MIN
Α	0.900	0.700	0.035	0.028
b	0.350	0.240	0.014	0.009
c	0.250	0.100	0.010	0.004
D	3.450	3.050	0.136	0.120
D1	3.200	2.900	0.126	0.114
D2	1.850	1.350	0.073	0.053
Е	3.400	3.000	0.134	0.118
E1	3.250	2.900	0.128	0.114
E2	2.600	2.350	0.102	0.093
e	0.65	0.65BSC		6BSC
Н	0.500	0.300	0.020	0.012
L	0.500	0.300	0.020	0.012
L1	0.200	0.070	0.008	0.003
θ	12°	0 °	1 2 °	0°



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